# **Amplifier Transistors**

## **PNP Silicon**

### **Features**

• Pb-Free Packages are Available\*

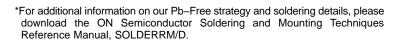
## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	-45	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	-50	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	-100	mAdc
Total Device Dissipation  @ T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	350 2.8	mW mW/°C
Total Device Dissipation  @ T <sub>C</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

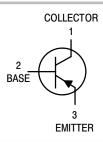
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction–to–Case	$R_{ heta JC}$	125	°C/W





### ON Semiconductor®

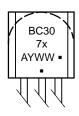
### http://onsemi.com





### MARKING DIAGRAM

TO-92 CASE 29 STYLE 17



BC307x = Device Code

x = B or C

A = Assembly Location

Y = Year WW = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BC307B	TO-92	5000 Units / Box
BC307BG	TO-92 (Pb-Free)	5000 Units / Box
BC307BRL1	TO-92	2000 / Tape & Reel
BC307BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC307BZL1	TO-92	2000 / Ammo Box
BC307BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC307C	TO-92	5000 Units / Box
BC307CG	TO-92 (Pb-Free)	5000 Units / Box

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•		•
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = -2.0 mAdc, I <sub>B</sub> = 0)		V <sub>(BR)CEO</sub>	-45	_	_	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = –100 μAdc, I <sub>C</sub> = 0)		V <sub>(BR)EBO</sub>	-5.0	_	_	Vdc
Collector–Emitter Leakage Current (V <sub>CES</sub> = -50 V, V <sub>BE</sub> = 0) (V <sub>CES</sub> = -50 V, V <sub>BE</sub> = 0) T <sub>A</sub> = 125°C		ICES	- -	-0.2 -0.2	-15 -4.0	nAdc μA
ON CHARACTERISTICS					•	•
DC Current Gain (I <sub>C</sub> = $-10 \mu Adc$ , V <sub>CE</sub> = $-5.0 Vdc$ )	BC307B BC307C	h <sub>FE</sub>	- -	150 270	- -	_
$(I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC307 BC307B BC307C		120 200 420	290 500	800 460 800	
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC307B BC307C		- -	180 300	_ _	
Collector – Emitter Saturation Voltage ( $I_C = -10 \text{ mAdc}$ , $I_B = -0.5 \text{ mAdc}$ ) ( $I_C = -10 \text{ mAdc}$ , $I_B = \text{see Note 1}$ ) ( $I_C = -100 \text{ mAdc}$ , $I_B = -5.0 \text{ mAdc}$ )		V <sub>CE(sat)</sub>	- - -	-0.10 -0.30 -0.25	-0.3 -0.6 -	Vdc
Base – Emitter Saturation Voltage ( $I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ( $I_C = -100$ mAdc, $I_B = -5.0$ mAdc)		V <sub>BE(sat)</sub>	- -	-0.7 -1.0	_ _	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = -2.0 mAdc, V <sub>CE</sub> = -5.0 Vdc)		V <sub>BE(on)</sub>	-0.55	-0.62	-0.7	Vdc
DYNAMIC CHARACTERISTICS					•	•
Current – Gain – Bandwidth Product (I <sub>C</sub> = –10 mAdc, V <sub>CE</sub> = –5.0 Vdc, f = 100 MHz)		f <sub>T</sub>	-	280	_	MHz
Common Base Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>cbo</sub>	-	_	6.0	pF
Noise Figure (I <sub>C</sub> = $-0.2$ mAdc, V <sub>CE</sub> = $-5.0$ Vdc, R <sub>S</sub> = $2.0$ k $\Omega$ , f = $1.0$ kHz)		NF	-	2.0	10	dB

<sup>1.</sup>  $I_C = -10$  mAdc on the constant base current characteristic, which yields the point  $I_C = -11$  mAdc,  $V_{CE} = -1.0$  V.

## **TYPICAL CHARACTERISTICS**

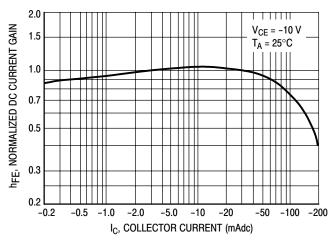


Figure 1. Normalized DC Current Gain

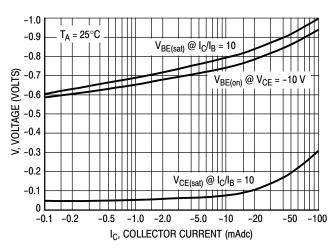


Figure 2. "Saturation" and "On" Voltages

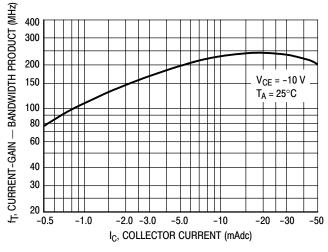


Figure 3. Current-Gain — Bandwidth Product

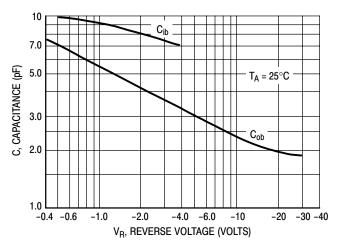


Figure 4. Capacitances

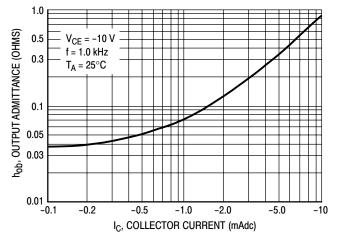


Figure 5. Output Admittance

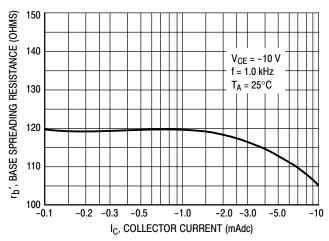
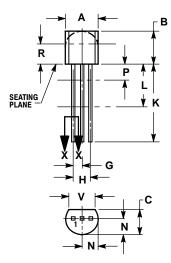


Figure 6. Base Spreading Resistance

### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL** 





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
v	0 135		2 //2		

STYLE 17:

PIN 1. COLLECTOR

BASE

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